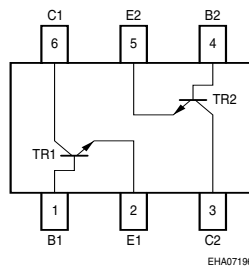
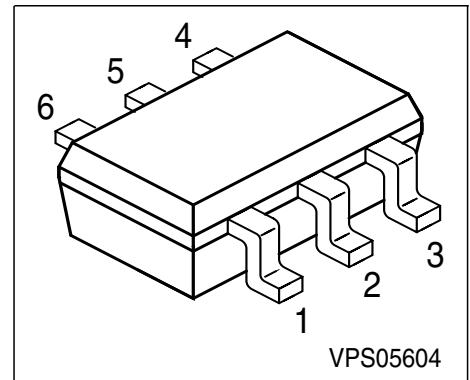


NPN Silicon RF Transistor

- For low noise, low-power amplifiers in mobile communication systems (pager, cordless telephone) at collector currents from 0.2 mA to 8 mA
- $f_T = 7 \text{ GHz}$
 $F = 1.5 \text{ dB at } 900 \text{ MHz}$
- Two (galvanic) internal isolated Transistors in one package



ESD: Electrostatic discharge sensitive device, observe handling precaution!

Type	Marking	Pin Configuration						Package
BFS 480	REs	1=B	2=E	3=C	4=B	5=E	6=C	SOT-363

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	8	V
Collector-emitter voltage	V_{CES}	10	
Collector-base voltage	V_{CBO}	10	
Emitter-base voltage	V_{EBO}	2	
Collector current	I_C	10	mA
Base current	I_B	1.2	
Total power dissipation, $T_S \leq 112^\circ\text{C}^1$	P_{tot}	80	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Ambient temperature	T_A	-65 ... 150	
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Junction - soldering point	R_{thJS}	≤ 470	K/W
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¹ T_S is measured on the collector lead at the soldering point to the pcb

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC characteristics					
Collector-emitter breakdown voltage $I_C = 1\text{ mA}$, $I_B = 0$	$V_{(BR)CEO}$	8	-	-	V
Collector-emitter cutoff current $V_{CE} = 10\text{ V}$, $V_{BE} = 0$	I_{CES}	-	-	100	μA
Collector-base cutoff current $V_{CB} = 8\text{ V}$, $I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 1\text{ V}$, $I_C = 0$	I_{EBO}	-	-	1	μA
DC current gain $I_C = 3\text{ mA}$, $V_{CE} = 5\text{ V}$	h_{FE}	30	100	200	-

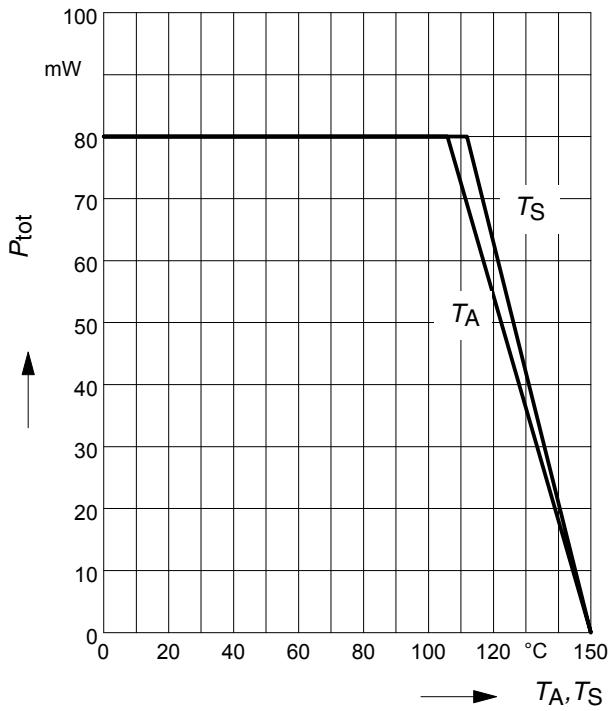
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC characteristics (verified by random sampling)					
Transition frequency $I_C = 6\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 500\text{ MHz}$	f_T	5	7.5	-	GHz
Collector-base capacitance $V_{CB} = 5\text{ V}$, $f = 1\text{ MHz}$	C_{cb}	-	0.23	0.4	pF
Collector-emitter capacitance $V_{CE} = 5\text{ V}$, $f = 1\text{ MHz}$	C_{ce}	-	0.1	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$	C_{eb}	-	0.23	-	
Noise figure $I_C = 1.5\text{ mA}$, $V_{CE} = 5\text{ V}$, $Z_S = Z_{Sopt}$, $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$	F	- -	1.5 2	- -	dB
Power gain, maximum stable ^{F)} $I_C = 3\text{ mA}$, $V_{CE} = 5\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$	G_{ms}	- -	18 14	- -	
Transducer gain $I_C = 3\text{ mA}$, $V_{CE} = 5\text{ V}$, $Z_S = Z_L = 50\Omega$, $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$	$ S_{21e} ^2$	- -	14 9.5	- -	

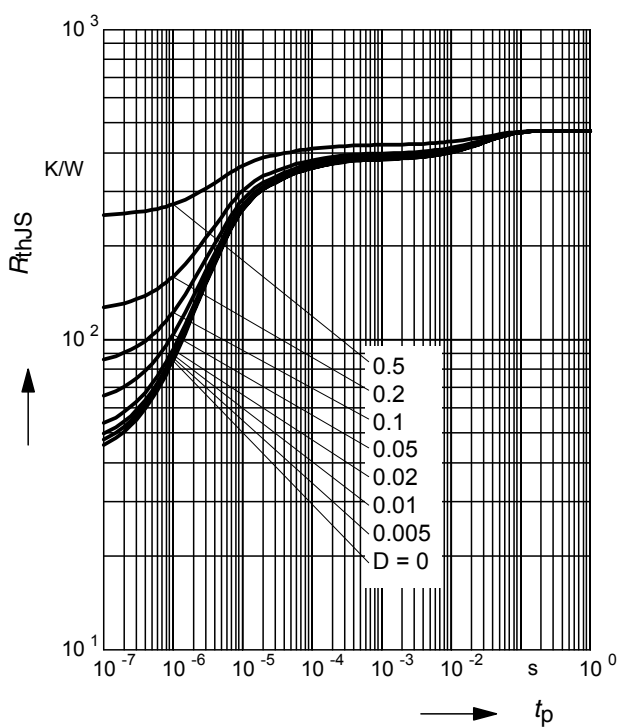
$$^1G_{ms} = |S_{21} / S_{12}|$$

Total power dissipation $P_{\text{tot}} = f(T_A^*, T_S)$

* Package mounted on epoxy

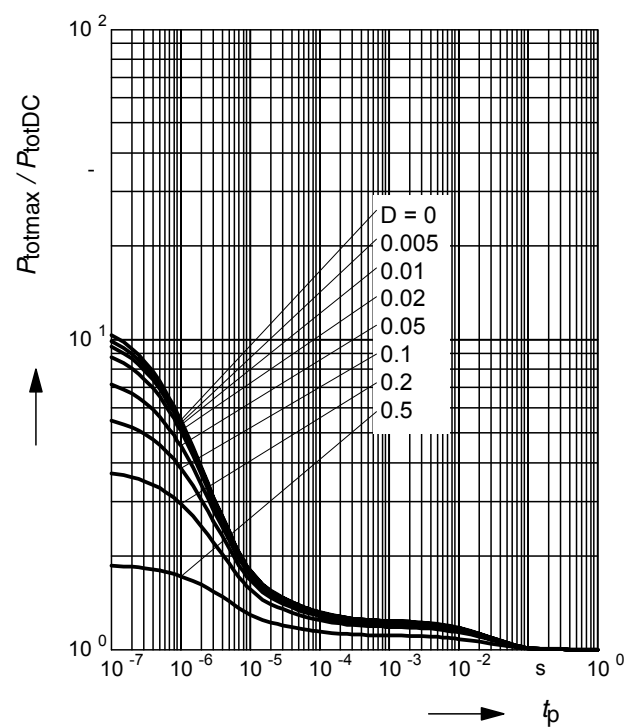


Permissible Pulse Load $R_{\text{thJS}} = f(t_p)$



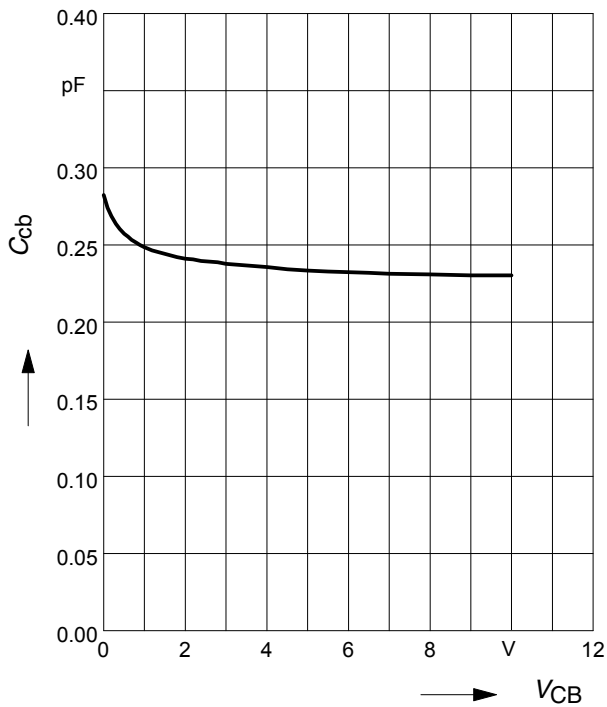
Permissible Pulse Load

$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$



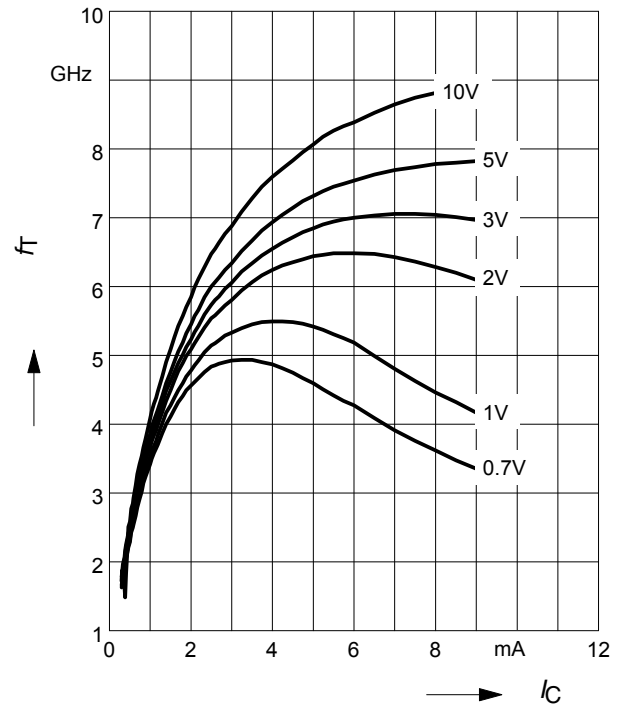
Collector-base capacitance $C_{cb} = f(V_{CB})$

$f = 1\text{MHz}$



Transition frequency $f_T = f(I_C)$

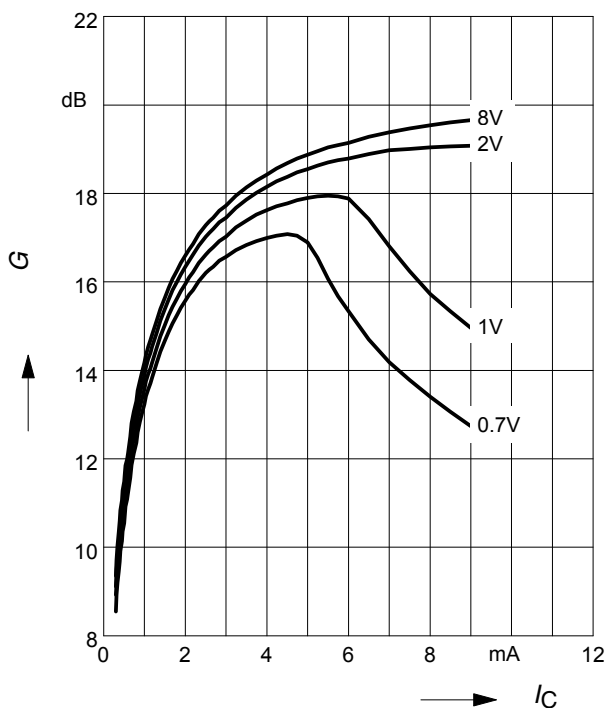
$V_{CE} = \text{Parameter}$



Power Gain $G_{ma}, G_{ms} = f(I_C)$

$f = 0.9\text{GHz}$

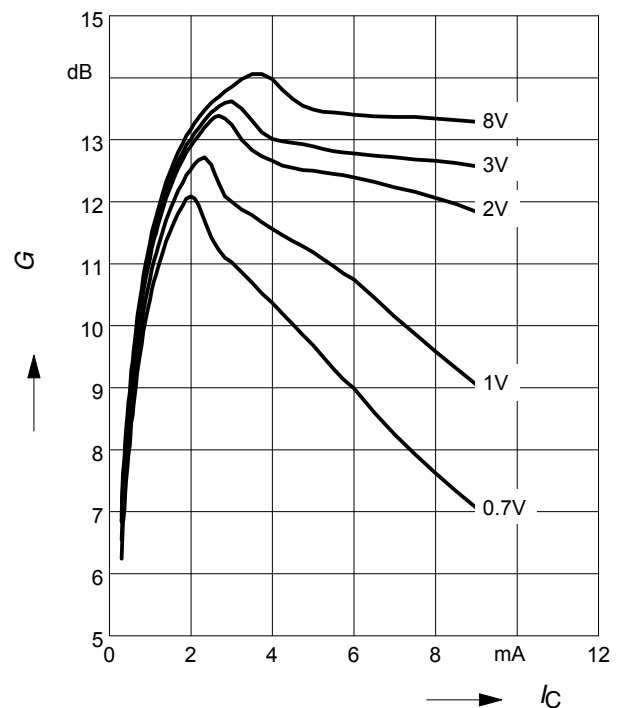
$V_{CE} = \text{Parameter}$



Power Gain $G_{ma}, G_{ms} = f(I_C)$

$f = 1.8\text{GHz}$

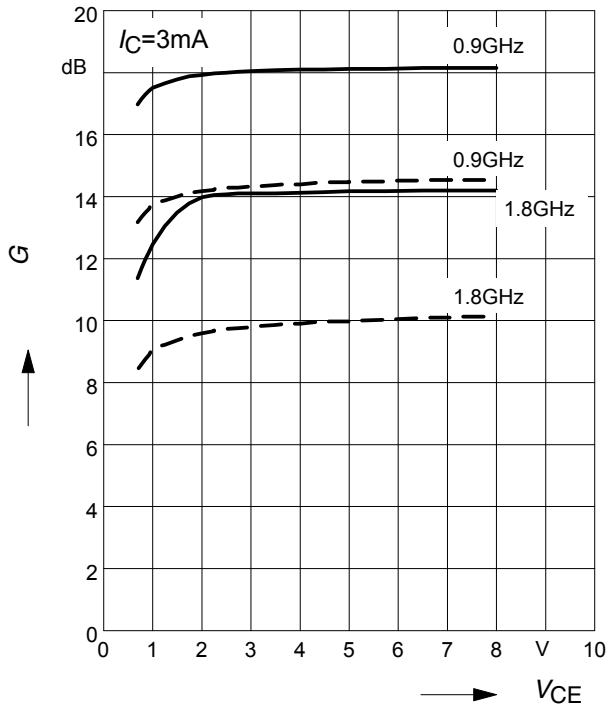
$V_{CE} = \text{Parameter}$



Power Gain $G_{ma}, G_{ms} = f(V_{CE})$:

$|S_{21}|^2 = f(V_{CE})$:

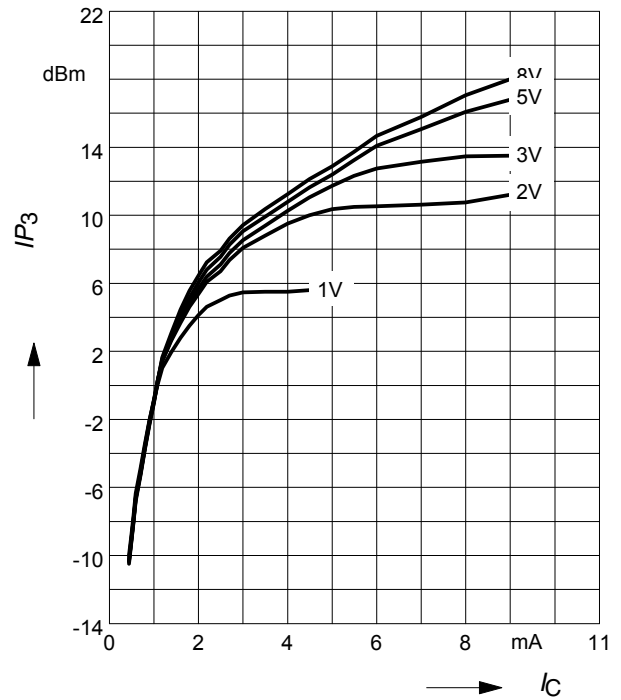
f = Parameter



Intermodulation Intercept Point $IP_3 = f(I_C)$

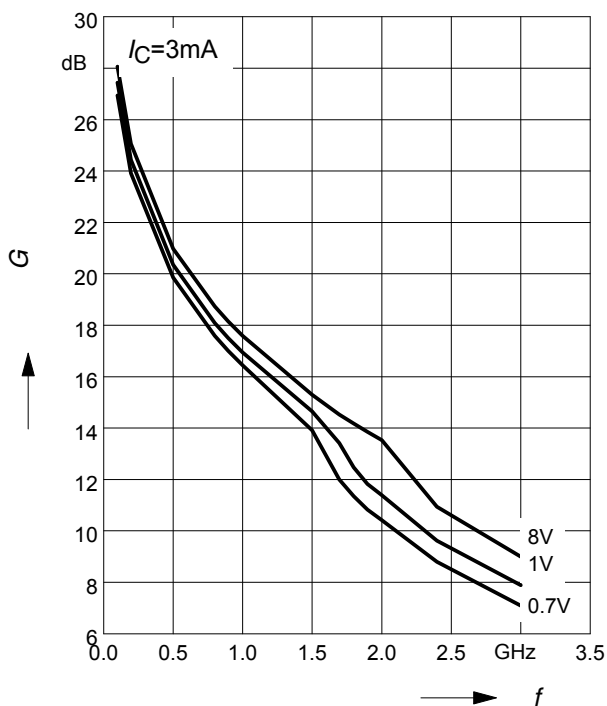
(3rd order, Output, $Z_S = Z_L = 50\Omega$)

V_{CE} = Parameter, $f = 900\text{MHz}$



Power Gain $G_{ma}, G_{ms} = f(f)$

V_{CE} = Parameter



Power Gain $|S_{21}|^2 = f(f)$

V_{CE} = Parameter

